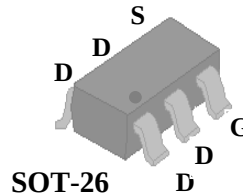




- ▼ Fast Switching Characteristic
- ▼ Lower Gate Charge
- ▼ Small Footprint & Low Profile Package

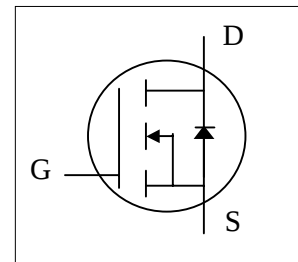


BV_{DSS}	150V
$R_{DS(ON)}$	2.6Ω
I_D	0.57A

Description

Advanced Power MOSFETs utilized advanced processing techniques to achieve the lowest possible on-resistance, extremely efficient and cost-effectiveness device.

The SOT-26 package is widely used for commercial-industrial surface mount applications.



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	150	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_A=25^\circ\text{C}$	Continuous Drain Current ³ , V_{GS} @ 10V	0.57	A
$I_D@T_A=70^\circ\text{C}$	Continuous Drain Current ³ , V_{GS} @ 10V	0.45	A
I_{DM}	Pulsed Drain Current ¹	2	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation	2	W
	Linear Derating Factor	0.016	W/ $^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Value	Unit
Rthj-a	Maximum Thermal Resistance, Junction-ambient ³	62.5	$^\circ\text{C}/\text{W}$



AP2608GY

Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =1mA	150	-	-	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =0.5A	-	-	2.6	Ω
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	1	-	3	V
g _{fs}	Forward Transconductance	V _{DS} =10V, I _D =0.6A	-	0.6	-	S
I _{DSS}	Drain-Source Leakage Current	V _{DS} =150V, V _{GS} =0V	-	-	25	uA
	Drain-Source Leakage Current (T _j =70°C)	V _{DS} =120V, V _{GS} =0V	-	-	100	uA
I _{GSS}	Gate-Source Leakage	V _{GS} = ±20V, V _{DS} =0V	-	-	±100	nA
Q _g	Total Gate Charge ²	I _D =0.5A	-	3	4.8	nC
Q _{gs}	Gate-Source Charge	V _{DS} =120V	-	0.5	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =10V	-	0.7	-	nC
t _{d(on)}	Turn-on Delay Time ²	V _{DS} =75V	-	7.4	-	ns
t _r	Rise Time	I _D =0.5A	-	6.5	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =3.3Ω, V _{GS} =10V	-	58	-	ns
t _f	Fall Time	R _D =150Ω	-	26	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	80	130	pF
C _{oss}	Output Capacitance	V _{DS} =25V	-	17	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	3.7	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage ²	I _S =1.3A, V _{GS} =0V	-	-	1.5	V
t _{rr}	Reverse Recovery Time ²	I _S =1A, V _{GS} =0V,	-	57	-	ns
Q _{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	120	-	nC

Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test
- 3.Surface mounted on 1 in² copper pad of FR4 board t ≤ 10S ; 156°C/W when mounted on min. copper pad.

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

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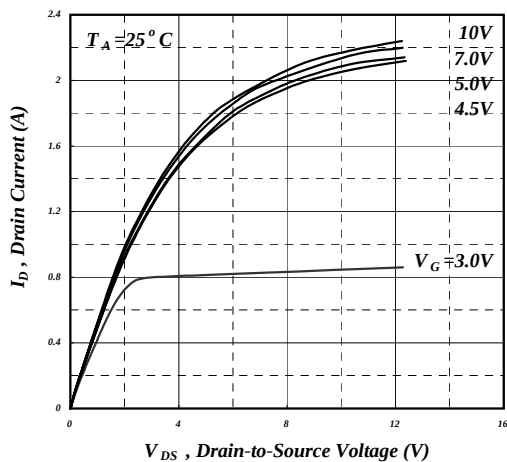


Fig 1. Typical Output Characteristics

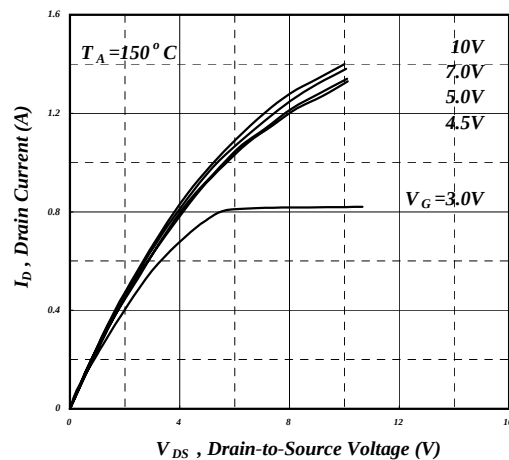


Fig 2. Typical Output Characteristics

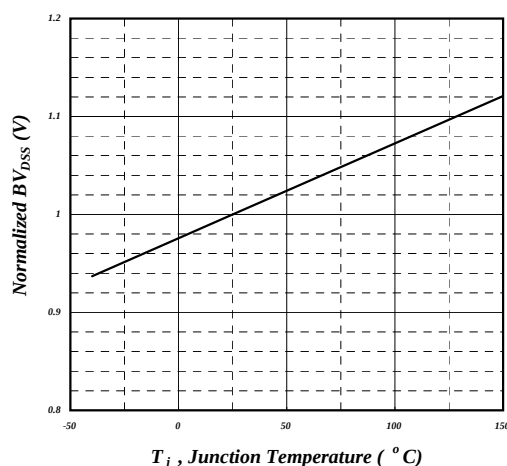


Fig 3. Normalized BV_{DSS} v.s. Junction Temperature

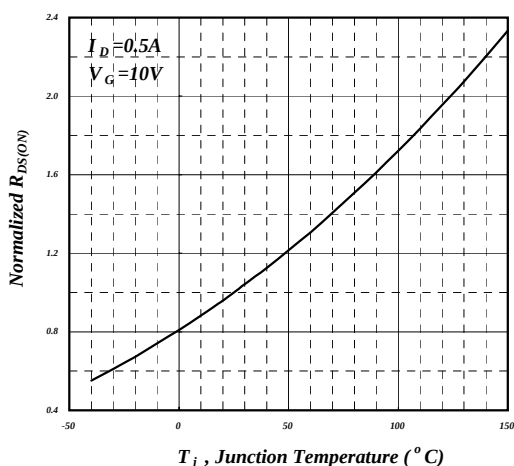


Fig 4. Normalized On-Resistance v.s. Junction Temperature

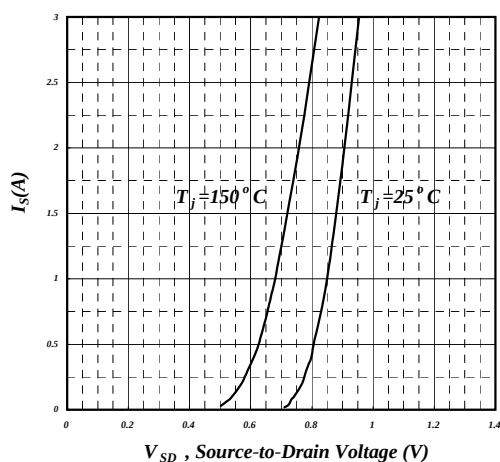


Fig 5. Forward Characteristic of Reverse Diode

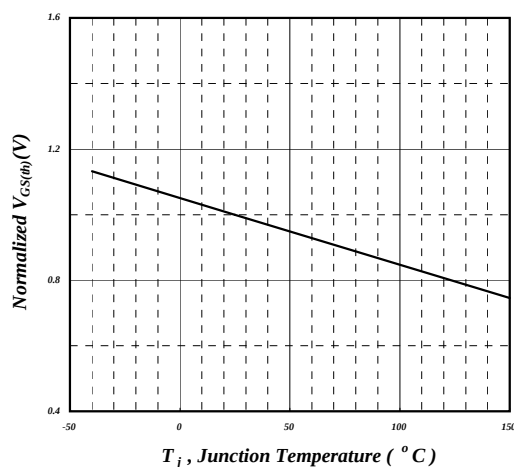


Fig 6. Normalized Gate Threshold Voltage v.s. Junction Temperature

